SEMICONDUCTOR

TECHNICAL DATA

S2AF ~ S2MF

Reverse Voltage - 50 to 1000 V, Forward Current - 2A

FEATURES

- For surface mounted applications
- Low profile package
- Glass Passivated Chip Juntion
- Lead free in comply with EU RoHS 2011/65/EU directives
- Plastic package bas underwriters laboratory flammability classification 94V-0
- AEC-Q101 qualified

MECHANICAL DATA

■Case: SMA-FL

■ Terminals: Solderable per MIL-STD-750, Method 2026

SMA-FL 0.063(1.6) 0.106(2.7)0.051(1.3) 0.094(2.4) 0.146(3.7)0.130(3.3)0.193(4.9) 0.173(4.4) ∠5-7° 0.008(0.20) MAX 0.043(1.1) 0.035(0.9) 0.047(1.2) 0.031(0.8)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase half-wave 60 Hz, resistive or inductive load, for capacitive load current derate by 20 %.

Parameter	Symbols	S2AF	S2BF	S2DF	S2GF	S2JF	S2KF	S2MF	Units
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V _{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current at Ta = 65°C	I _{F(AV)}	2.0							А
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load (JEDEC Method)	I _{FSM}	50							А
Maximum Instantaneous Forward Voltage at 2 A	V _F	1.1							V
Maximum DC Reverse Current Ta = 25°C at Rated DC Blocking Voltage Ta = 125°C	I _R	5 50							μА
Typical Junction Capacitance 1)	C _j	10							pF
Typical Thermal Resistance 2)	R _{eJA}	80							°C/W
Operating and Storage Temperature Range	T_j, T_{stg}	-55 ~ +150							°C

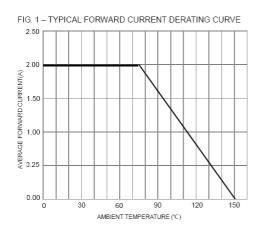
¹⁾ Measured at 1 MHz and applied reverse voltage of 4 V D.C

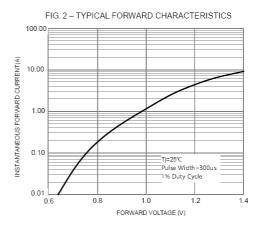
Revision No: 0

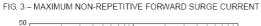
^{2)} Thermal resistance from junction to ambient at 0.375" (9.5 mm) lead length, P.C.B. mounted $\,$

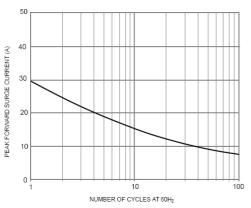


S2AF ~ **S2MF**









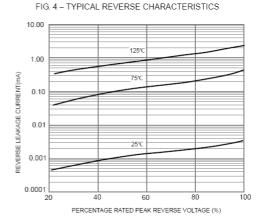


FIG. 5 - TYPICAL JUNCTION CAPACITANCE

